Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSIII)

2SK2700

Chopper Regulator, DC–DC Converter and Motor Drive Applications

• Low drain—source ON resistance : R_{DS} (ON) = 3.7 Ω (typ.) • High forward transfer admittance : $|Y_{fs}| = 2.6 \text{ S}$ (typ.) • Low leakage current : $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 720 \text{ V}$)

• Enhancement–mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	900	V
Drain-gate voltage (Ro	_{GS} = 20 kΩ)	V_{DGR}	900	V
Gate-source voltage		V_{GSS}	±30	٧
Drain current	DC (Note 1)	I _D	3	Α
	Pulse (Note 1)	I _{DP}	9	Α
Drain power dissipatio	n (Tc = 25°C)	P _D	40	W
Single pulse avalanche	e energy (Note 2)	E _{AS}	295	mJ
Avalanche current		I _{AR}	3	Α
Repetitive avalanche	energy (Note 3)	E _{AR}	4	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature ra	ange	T _{stg}	-55~150	°C

1. GATE 2. DRAIN 3. SOURCE JEDEC JEITA SC-67 TOSHIBA 2.7±0.2

Weight: 1.9 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

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Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 60.0 mH, R_G = 25 Ω , I_{AR} = 3 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

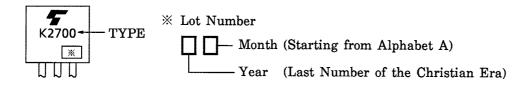
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V _(BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cur	rent	I _{DSS}	V _{DS} = 720 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source bro	eakdown voltage	V _{(BR)DSS}	I_D = 10 mA, V_{GS} = 0 V	900	_	_	V
Gate threshold v	roltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source Of	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 1.5 A	_	3.7	4.3	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 20 V, I _D = 1.5 A	0.65	2.6	_	S
Input capacitanc	е	C _{iss}			750	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	10	_	
Output capacitance		C _{oss}			70	_	
Switching time	Rise time	t _r	V _{GS} _{0V} I _D =1.5A _{Out} _{RL} =133Ω	_	15	_	ns
	Turn-on time	t _{on}		_	55	_	
	Fall time	t _f		_	30	_	
	Turn-off time	t _{off}	$V_{DD} = 200V$ $Duty \le 1\%, \ t_w = 10 \mu s$	_	110	_	
Total gate charg plus gate–drain)	-			25			
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		13	_	nC
Gate-drain ("miller") Charge		Q_{gd}			12	_	

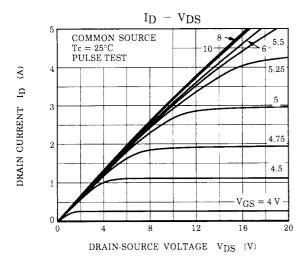
Source-Drain Ratings and Characteristics (Ta = 25°C)

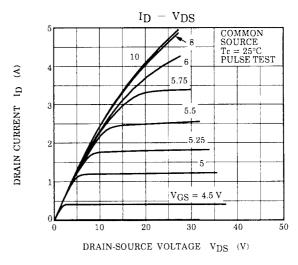
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	-	_	_	3	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	9	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 3 A, V _{GS} = 0 V	_	_	-1.9	V
Reverse recovery time	t _{rr}	I _{DR} = 3 A, V _{GS} = 0 V		1100	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	_	7.2	_	μC

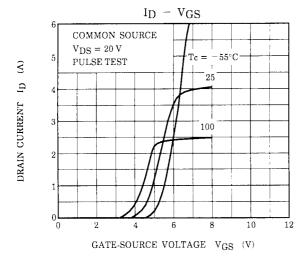
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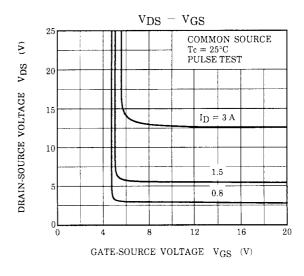


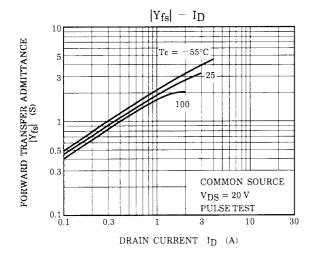
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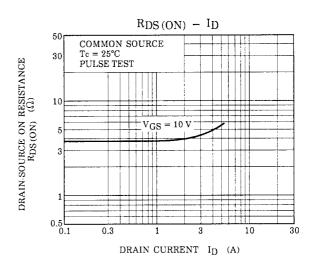




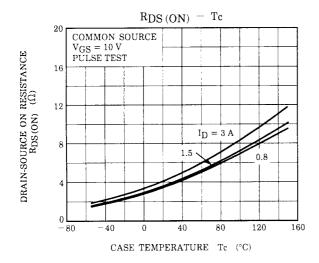


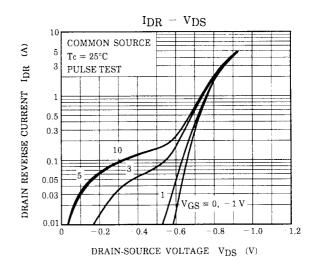


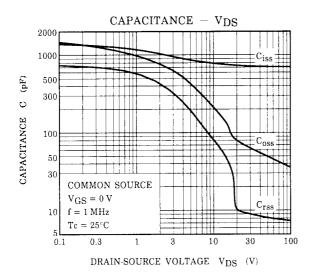


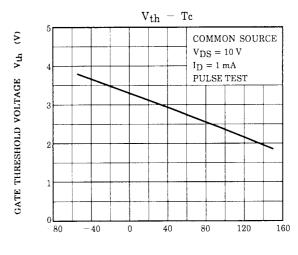


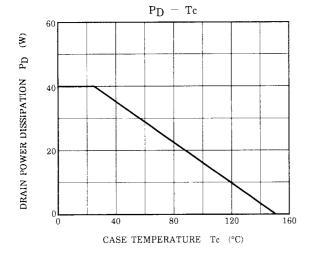
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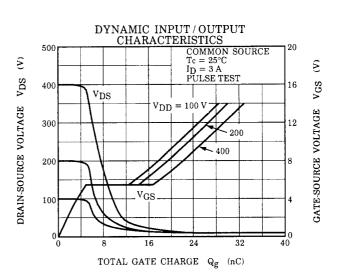




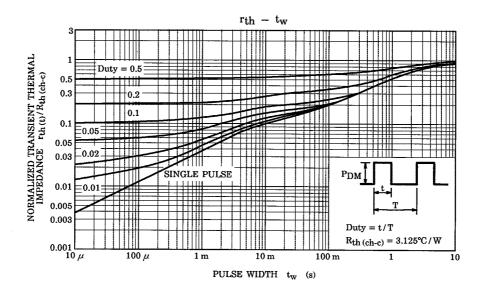


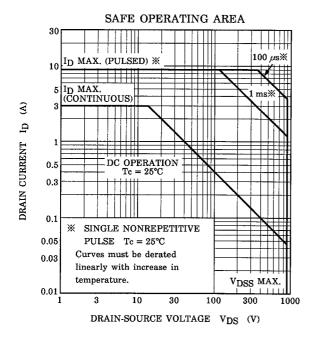


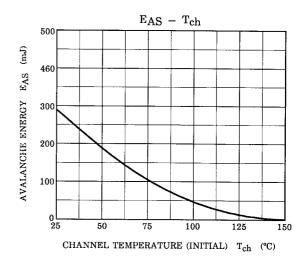


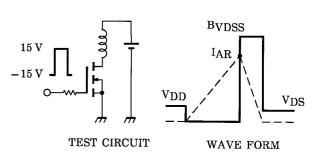


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$$R_G = 25 \Omega$$

 $V_{DD} = 90 \text{ V}, L = 60 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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